Approved	Checked	Designed	DEVELOPMENT SPECIFICATION	
T. Akeda		T. Takata	P/N : LNJ416Q8YRU	

TYPE	Amber Light Emitting Diode
APPLICATION	Indicators
MATERIAL	GaAsP
OUTLINE	Attached

ABSOLUTE MAXIMUM RATINGS	P	※ I_{FP}	I_{FDC}	V_R	Topr	Tstg
	60 mW	100 mA	20 mA	4 V	-30～+85 ℃	-40～+100 ℃

CONDITION : Ta = 25 ± 3℃

Test Specification

Item	Symbol	Condition	Typ	Limit		Unit
				Min	Max	
Forward Voltage	V_F	I_F = 10 mA	2.0		2.6	V
Reverse Leakage Current	I_R	V_R = 4 V			10	μA
Luminous Intensity	I_O	I_F = 10 mA・DC	3.3	1.2		mcd
Peak Emission Wavelength	λp	I_F = 10 mA・DC	590			nm
Spectral Line Half Width	Δλ	I_F = 10 mA・DC	30			nm

※ ・ The Condition of I_{FP} is duty 10 %, Pulse width 1 ms

・ Please contact the Panasonic local office if you design at low current (below 1 mA DC) or pulse current operation and have any questions.

NOTE

1. Soldering conditions.
   Refer to Handling note.
2. Care should be taken that soldering is done within 3-days after opening the dry package and reel.
3. Compositions of the lead····Cu/Ni/Au plating
4. Lens : Yellow clear type

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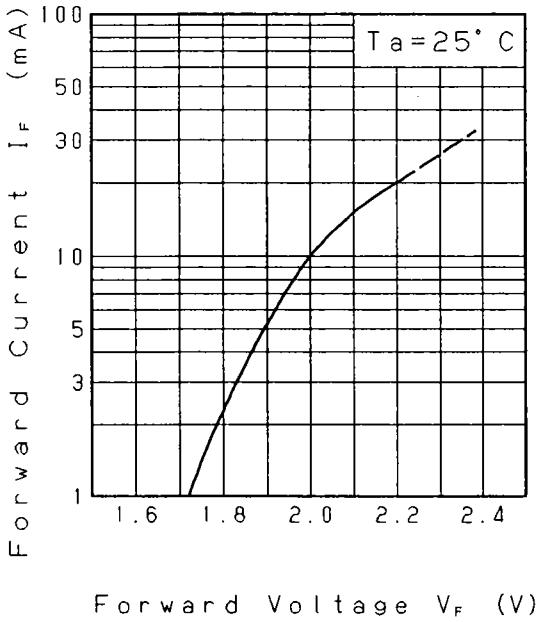
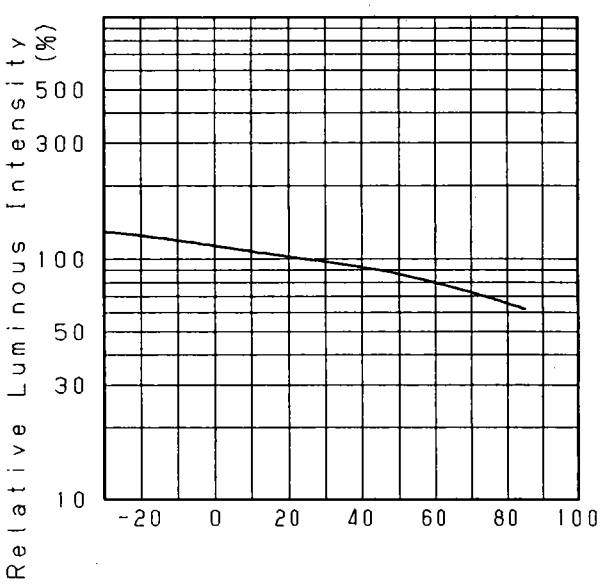
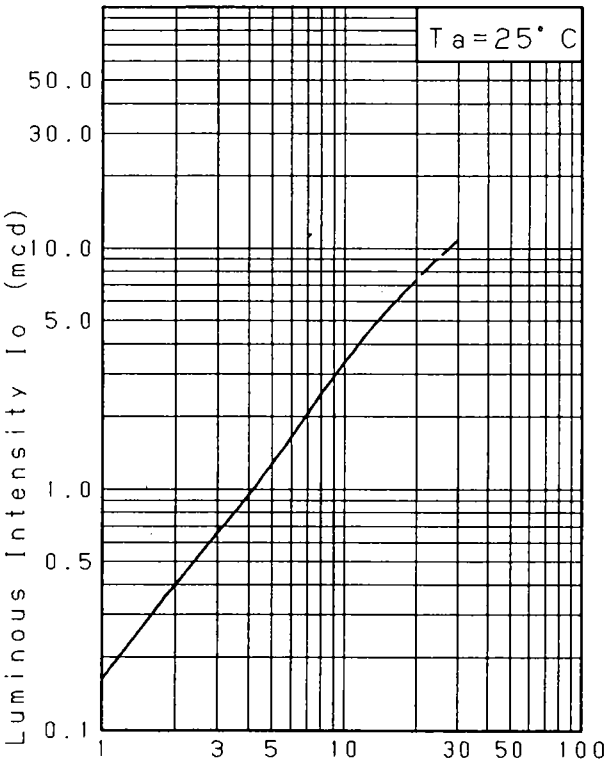
I_F - V_F



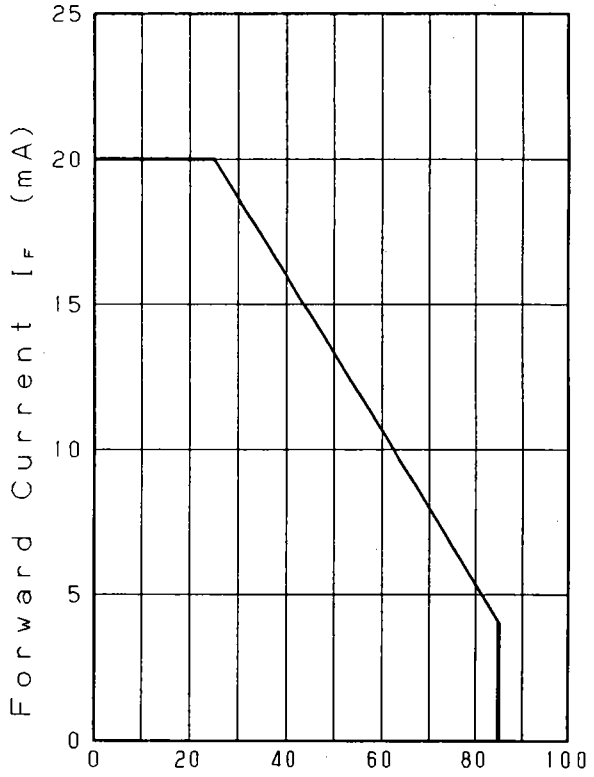
I_O - Ta



Io - I_F



I_F - Ta



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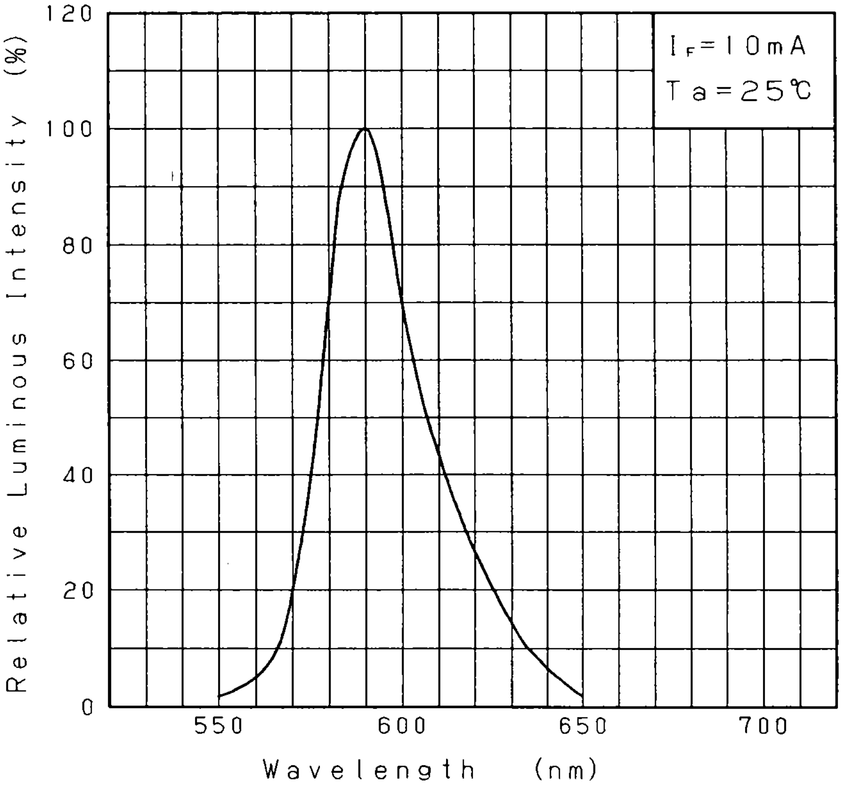
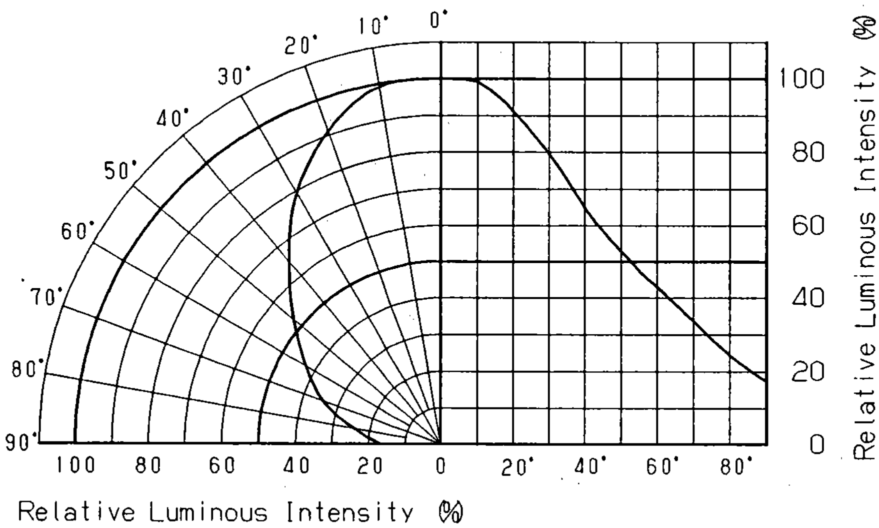
T. Ikeda	[signature]	T. Tabata	P/N:LNJ416Q8YRU

Relative Luminous Intensity Wavelength Characteristics



Directive Characteristics



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T. Okada	H. Iwai	T. Tabata

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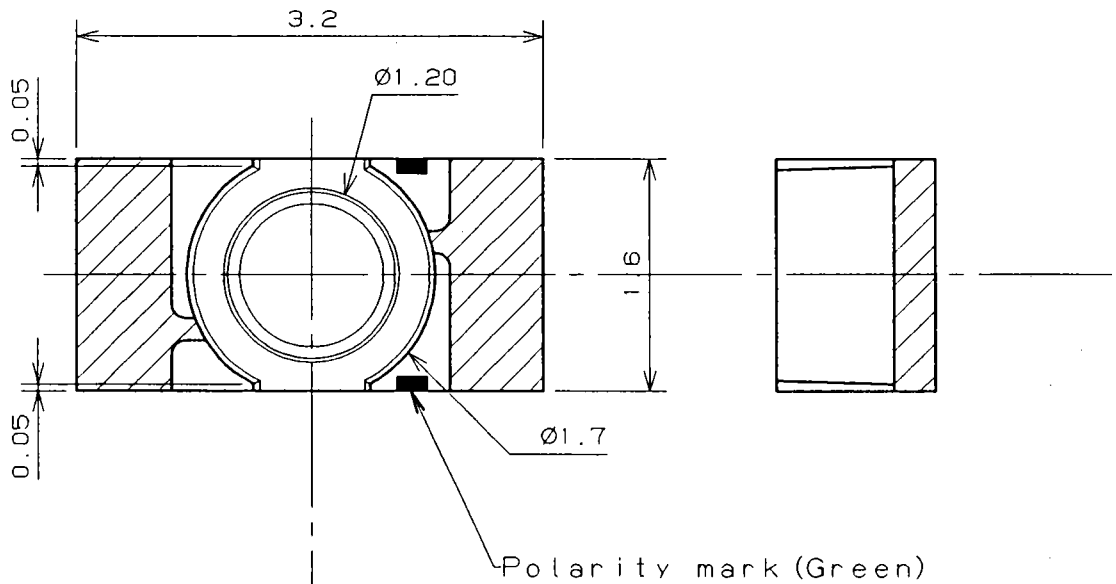
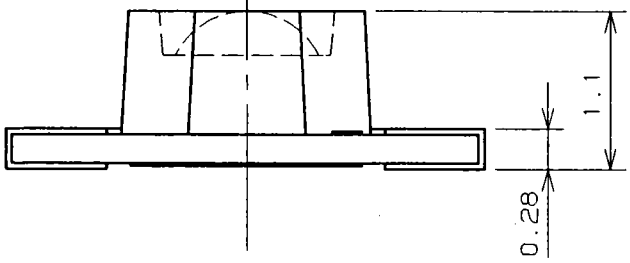
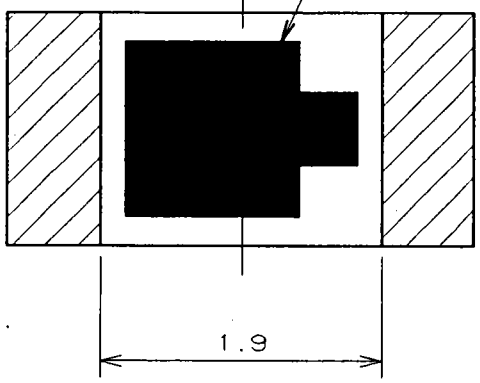
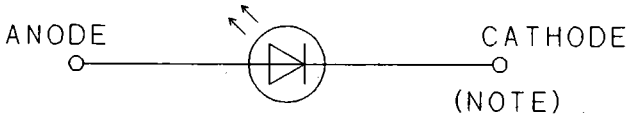
(OUTLINE)
P/N: LNJ416Q8YRU





Polarity mark (Green)





(NOTE)
1. Unit: mm
2. Tolerance unless specified is ±0.15.
3. ▨ indicate Au terminal.

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